L Number	Hits	Search Text	DB	Time stamp
1	2496	257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls.	USPAT;	2004/05/25 09:48
·		257/762.ccls.	US-PGPUB	
2	414	(msq (methyl adj silsesquioxane)) and ((barrier with	USPAT;	2004/05/25 09:59
•		(dielectric insulator carbide nitride oxide oxynitride))	US-PGPUB;	
		electromigration diffusion)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	231	((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj	USPAT;	2004/05/25 10:55
		silicon adj carbide) "sic(h)") and ((barrier with (dielectric	US-PGPUB;	
		insulator carbide nitride oxide oxynitride)) electromigration	EPO; JPO;	
		diffusion)	DERWENT;	
			IBM_TDB	
5	64	((polymeric adj alkyl adj siloxane) sioch sicoh) and	USPAT;	2004/05/25 11:16
	ļ	((polymeric adj silicon adj carbide) "sic(h)")	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
ŀ			IBM_TDB	
6	33	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls.	USPAT;	2004/05/25 11:21
]		257/762.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh	US-PGPUB;	
	ĺ	sioch (polymeric adj silicon adj carbide) "sic(h)")	EPO; JPO;	
			DERWENT;	
_		(0=-(1 100(b 1) 1// 1 1 1 1 1 1 1 1 1	IBM_TDB	2004/05/25 11.25
7	234	(257/\$.ccls. 438/\$.ccls.) and ((polymeric adj alkyl adj	USPAT;	2004/05/25 11:25
		siloxane) sicoh sioch sich (polymeric adj silicon adj carbide)	US-PGPUB;	
		"sic(h)")	EPO; JPO;	
	•		DERWENT;	
	45	BATIVA CT IV BATIVA CT IVA ODI I	IBM_TDB USPAT;	2004/05/25 11:47
8	45	MIKAGI-K MIKAGI-KAORU	US-PGPUB;	2004/05/25 11:47
			EPO; JPO;	
			DERWENT	
	45	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls.	USPAT;	2004/05/25 11:51
9	45	(257/751.ccis. 257/752.ccis. 257/759.ccis. 257/760.ccis. 257/762.ccis.) and ((silicon wafer semiconductor) and	US-PGPUB	200 1/05/25 11.51
	!	(damascene inlaid "in-laid") and ((copper cu) same seed	33 1 3 1 3 1	
		same (electroplat\$3 plat43) same (cmp planar\$8)))		
10	47	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls.	USPAT;	2004/05/25 12:02
10	7/	257/762.ccls.) and (((dielectric insulat\$4 oxide dioxide sioch	US-PGPUB	250 1, 05, 25 22.02
		sicoh sich "low-k" "low k") near4 barrier) with (reduc\$5	55 , 5, 55	
		redox deoxid\$7))	,	
	1	I ICUON GCONIGP/ //	·	